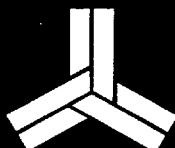


**High-Performance  
32Kx32 Burst Synchronous  
CMOS SRAM**



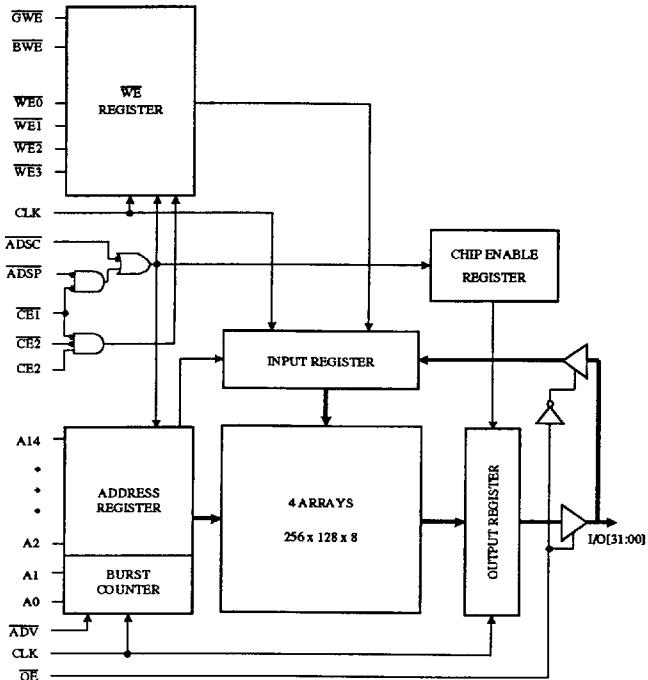
**AS7C33232  
AS7C33232L**

**ADVANCE INFORMATION  
32Kx32 Synchronous Pipelined Burst SRAM**

**FEATURES**

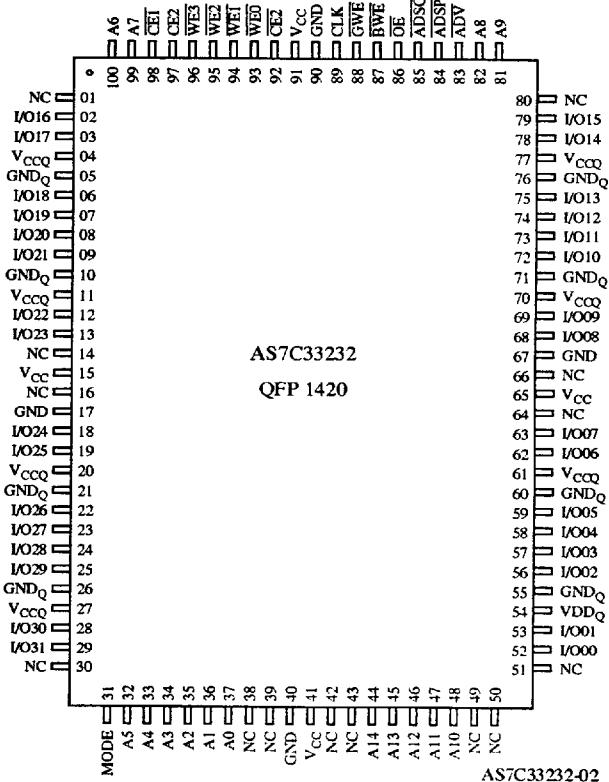
- Organization: 32,768 words × 32 bits
- Fully synchronous pipelined operation
- Fast clocking speed: 75/66/60 MHz
- Fast clock to data access: 6/7/8 ns
- Self-timed write cycle
- On-chip address, control, and data registers
- Byte write enable & global write enable control
- Asynchronous output enable control
- ADSP, ADS<sub>C</sub>, ADV burst control pins
- Pentium<sup>TM</sup> or PowerPC<sup>TM</sup> count sequence
- Transparent logic support for 1 or 2 CPUs
- Single 3.3 ±0.3V power supply
- 5V safe inputs
- ESD protection >2000 volts
- Latch-up current > 200 mA

**LOGIC BLOCK DIAGRAM**



AS7C33232-01

**PIN ARRANGEMENT**



AS7C33232-02

**SELECTION GUIDE**

	<b>7C33232-13</b>	<b>7C33232-15</b>	<b>7C33232-17</b>	<b>Unit</b>
Minimum cycle time	13.3	15	16.6	ns
Maximum clock frequency	75	66	60	MHz
Maximum output enable access time	5	6	7	ns
Maximum operating current	280	240	220	mA
Maximum standby current	30	30	30	mA
Maximum CMOS standby current (DC)	6	6	6	mA
	L	3	3	mA

**ALLIANCE SEMICONDUCTOR**

9003449 0000104 T1T



## FUNCTIONAL DESCRIPTION

The AS7C33232 is a high performance CMOS 1,024,576-bit synchronous Static Random Access Memory (SRAM) organized as 32,768 words  $\times$  32 bits, and incorporating a 2-bit burst counter and output register. It is designed for high performance 3.3V Pentium™ and PowerPC™ cache applications.

Fast cycle times of 13/15/17 ns with output enable access times ( $t_{OE}$ ) of 5/6/7 ns are ideal for 75, 66, and 60 MHz bus frequencies. Three chip enable inputs permit easy memory expansion. Burst operation is initiated in one of two ways: the controller address strobe (ADSC), or the processor address strobe (ADSP). The burst advance pin (ADV) allows subsequent internally generated burst addresses.

Read cycles are initiated with ADSP (regardless of WE and ADSC) using the new external address clocked into the on-chip address register when ADSP is sampled LOW, the chip selects are sampled active, and the output buffer is enabled with OE. In a read operation the data accessed by the current address, registered in the address registers by the positive edge of CLK, are carried to the data-out registers on the next positive edge of CLK and driven on the output pins. ADV is ignored on the clock edge that samples ADSP asserted, but is sampled on all subsequent clock edges. Address is incremented internally for the next access of the burst when WE is sampled HIGH, ADV is sampled LOW, and both address strobes are HIGH.

Write cycles are performed by disabling the output buffers with OE and asserting WE. A global write enable GWE writes all 32 bits regardless of the state of individual WE0-WE3 inputs. Alternately, when GWE is HIGH, one or more bytes may be written by asserting

BWE and the appropriate individual byte WE signal(s). WE0 controls I/O0-I/O7; WE1 controls I/O8-I/O15; WE2 controls I/O16-I/O23; and WE3 controls I/O24-I/O31.

WE is ignored on the clock edge that samples ADSP LOW, but is sampled on all subsequent clock edges. Output buffers are disabled when WE is sampled LOW (regardless of OE). Data is clocked into the data input register when WE is sampled LOW. Address is incremented internally to the next burst of address if WE and ADV are sampled LOW.

Read or write cycles may also be initiated with ADSC instead of ADSP. The differences between cycles initiated with ADSC and ADSP follow.

- ADSP must be sampled HIGH when ADSC is sampled LOW to initiate a cycle with ADSC.
- WE signals are sampled on the clock edge that samples ADSC LOW (and ADSP HIGH).
- Master chip select CE1 blocks ADSP, but not ADSC.

Burst operation is selectable with the MODE input. With MODE unconnected or driven HIGH burst operations use a Pentium/486 count sequence. With MODE driven LOW the device uses a linear count sequence, suitable for PowerPC and many other applications (refer to the Burst Sequence Table on page 3).

The AS7C33232 operates from a single 3.3±0.3V supply. Inputs and outputs are TTL compatible and 5V tolerant. The AS7C33232 is packaged in a 100 pin 14x20 mm QFP package.

## SIGNAL DESCRIPTIONS

Signal	I/O	Properties	Description
CLK	I	CLOCK	Clock. All inputs except OE are synchronous to this clock.
A0-A14	I	SYNC	Address. Sampled when all chip enables are active and ADSC or ADSP are asserted.
I/O0-I/O31	I/O	SYNC	Data. Driven as output when the chip is enabled and OE is active.
CE1	I	SYNC	Master Chip Enable. Sampled on clock edges when ADSP or ADSC is active. When CE1 is inactive, ADSP is blocked. Refer to the SYNCHRONOUS TRUTH TABLE for more information.
CE2, CE2	I	SYNC	Synchronous chip enables. Active HIGH and active LOW, respectively. Sampled on clock edges when ADSC is active or when CE1 and ADSP are active.
ADSP	I	SYNC	Address status processor. Asserted LOW to load a new bus address or to enter standby mode.
ADSC	I	SYNC	Address status controller. Asserted LOW to load a new address or to enter standby mode.
ADV	I	SYNC	Advance. Asserted LOW to continue burst read/write.
GWE	I	SYNC default = HIGH	Global write enable. Asserted LOW to write all 32 bits. When HIGH, BWE and WE0-WE3 control write enable. This signal is internally pulled HIGH.
BWE	I	SYNC default = LOW	Byte write enable. Asserted LOW with GWE = HIGH to enable effect of WE0-WE3 inputs. This signal is internally pulled LOW.
WE0-WE3	I	SYNC	Write enables. Used to control write of individual bytes when GWE = HIGH and BWE = LOW. If any of WE0-WE3 is active with GWE = HIGH and BWE = LOW the cycle is a write cycle. If all WE0-WE3 are inactive the cycle is a read cycle.
OE	I	ASYNC	Asynchronous output enable. I/O pins are driven when OE is active and the chip is synchronously enabled.
MODE	I	STATIC default = HIGH	Count mode. When driven HIGH, count sequence follows Intel XOR convention. When driven LOW, count sequence follows Motorola/linear convention. This signal is internally pulled HIGH.



### SYNCHRONOUS TRUTH TABLE

<b>CE1</b>	<b>CE2</b>	<b>CE2</b>	<b>ADSP</b>	<b>ADSC</b>	<b>ADV</b>	<b>WRITE<sub>n</sub></b>	<b>OE</b>	<b>Address Accessed</b>	<b>CLK</b>	<b>Operation</b>
H	X	X	X	L	X	X	X	NA	L to H	Deselect
L	L	X	L	X	X	X	X	NA	L to H	Deselect
L	L	X	H	L	X	X	X	NA	L to H	Deselect
L	X	H	L	X	X	X	X	NA	L to H	Deselect
L	X	H	H	L	X	X	X	NA	L to H	Deselect
L	H	L	L	X	X	F	L	External	L to H	Begin burst read
L	H	L	L	X	X	F	H	External	L to H	Begin burst read
L	H	L	H	L	X	F	L	External	L to H	Begin burst read
L	H	L	H	L	X	F	H	External	L to H	Begin burst read
X	X	X	H	H	L	F	L	Next	L to H	Cont. burst read
X	X	X	H	H	L	F	H	Next	L to H	Cont. burst read
X	X	X	H	H	H	F	L	Current	L to H	Suspend burst
X	X	X	H	H	H	F	H	Current	L to H	Suspend burst
H	X	X	X	H	L	F	L	Next	L to H	Cont. burst read
H	X	X	X	H	L	F	H	Next	L to H	Cont. burst read
H	X	X	X	H	H	F	L	Current	L to H	Suspend burst
H	X	X	X	H	H	F	H	Current	L to H	Suspend burst
L	H	L	H	L	X	T	X	External	L to H	Begin burst write
X	X	X	H	H	L	T	X	Next	L to H	Cont. burst write
H	X	X	X	H	L	T	X	Next	L to H	Cont. burst write
X	X	X	H	H	H	T	H	Current	L to H	Suspend burst write
H	X	X	X	H	H	T	H	Current	L to H	Suspend burst write

Key: X = Don't Care, L = LOW, H = HIGH, T = TRUE, F = FALSE.

### WRITE ENABLE TRUTH TABLE (per byte)

<b>GWE</b>	<b>BWE</b>	<b>WE<sub>n</sub></b>	<b>WRITE<sub>n</sub></b>
L	X	X	T
X	L	L	T
H	H	X	F
H	L	H	F

Key: X = Don't Care, L = LOW, H = HIGH.

### ASYNCHRONOUS OE TRUTH TABLE

<b>OE</b>	<b>I/O [31:0]</b>
L	Read data
H	HIGH-Z

Note: For write cycles that follow read cycles, output buffers must be disabled with OE to prevent data bus contention.

Key: L = LOW, H = HIGH.

### BURST SEQUENCE TABLE

		Mode = HIGH/No Connect Pentium Count Sequence				Mode = LOW Linear Count Sequence			
Start Address		00	01	10	11	00	01	10	11
Second Address		01	00	11	10	01	10	11	00
Third Address		10	11	00	01	10	11	00	01
Fourth Address		11	10	01	00	11	00	01	10

Note: The burst sequence wraps around to its initial state upon completion.



### **ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Min	Max	Unit
Power Supply Voltage relative to GND	V <sub>CC</sub>	-0.5	+4.6	V
Input Voltage relative to GND	V <sub>IN</sub>	-0.5	+6.0	V
Power Dissipation	P <sub>D</sub>	-	1.2	W
Storage Temperature (Plastic)	T <sub>stg</sub>	-55	+150	°C
Temperature under Bias	T <sub>bias</sub>	-10	+85	°C
DC Output Current	I <sub>out</sub>	-	20	mA

**NOTE:** Stresses greater than those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

### **RECOMMENDED OPERATING CONDITIONS**

(T<sub>a</sub> = 0°C to +70°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply Voltage	V <sub>CC</sub>	3.0	3.3	3.6	V
	GND	0.0	0.0	0.0	V
Input Voltage	V <sub>IH</sub>	2.2	-	5.5	V
	V <sub>IL</sub>	-0.5*	-	0.8	V

\* V<sub>IL</sub> min = -3.0V for pulse width less than t<sub>RC</sub>/2.

### **DC OPERATING CHARACTERISTICS**

(V<sub>CC</sub> = 3.3±0.3V, GND = 0V, T<sub>a</sub> = 0°C to +70°C)

Parameter	Symbol	Test Conditions	-13		-15		-17		Unit
			Min	Max	Min	Max	Min	Max	
Input Leakage Current	I <sub>LI</sub>	V <sub>CC</sub> = Max, V <sub>in</sub> = GND to V <sub>CC</sub>	-2	+2	-2	+2	-2	+2	µA
Output Leakage Current	I <sub>LO</sub>	OE ≥ V <sub>IH</sub> , V <sub>CC</sub> = Max, V <sub>out</sub> = GND to V <sub>CC</sub>	-2	+2	-2	+2	-2	+2	µA
Operating Power Supply Current	I <sub>CC</sub>	CE1 = V <sub>IL</sub> , CE2 = V <sub>III</sub> , CE2̄ = V <sub>IL</sub> , f = f <sub>max</sub> , I <sub>out</sub> = 0 mA	-	280	-	240	-	220	mA
Standby Power Supply Current	I <sub>SB</sub>	Deselected, f = f <sub>max</sub>	-	30	-	30	-	30	mA
	I <sub>SB1</sub>	Deselected, f = 0, all V <sub>IN</sub> ≤ 0.2V or ≥ V <sub>CC</sub> - 0.2V	-	6	-	6	-	6	mA
Output Voltage	V <sub>OL</sub>	I <sub>OL</sub> = 8 mA, V <sub>CC</sub> = Min	-	0.4	-	0.4	-	0.4	V
	V <sub>OH</sub>	I <sub>OH</sub> = -4 mA, V <sub>CC</sub> = Min	2.4	-	2.4	-	2.4	-	V

**CAPACITANCE<sup>1</sup>**(f = 1 MHz, T<sub>a</sub> = Room Temperature, V<sub>CC</sub> = 3.3±0.3V)

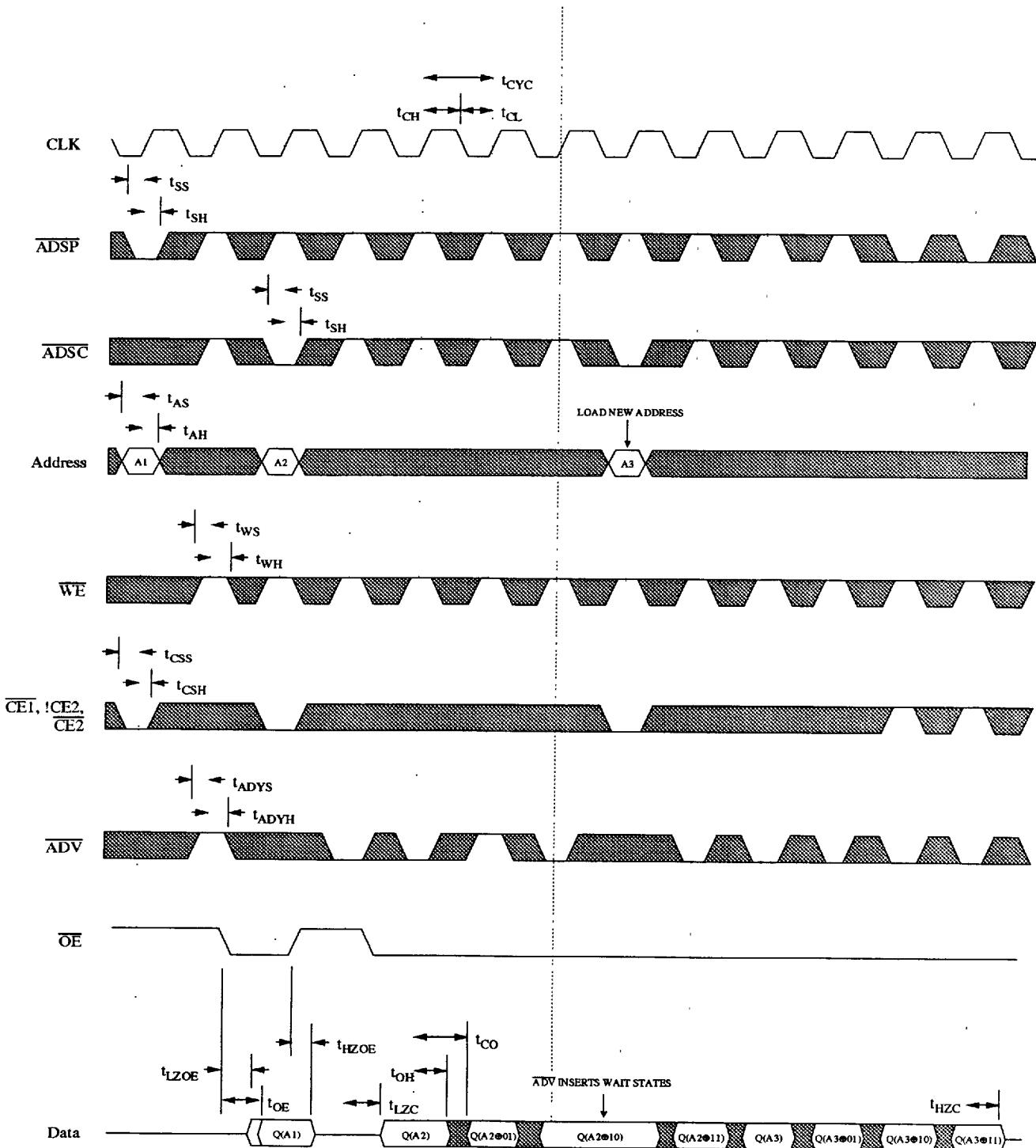
Parameter	Symbol	Signals	Test Conditions	Max	Unit
Input Capacitance	C <sub>IN</sub>	A, CE1, CE2, WE, OE, ADSP, ADSC, ADV	V <sub>in</sub> = 0V	5	pF
I/O Capacitance	C <sub>I/O</sub>	I/O	V <sub>in</sub> = V <sub>out</sub> = 0V	7	pF

**READ CYCLE, WRITE CYCLE, READ/WRITE CYCLE<sup>2</sup>** (V<sub>CC</sub> = 3.3±0.3V, GND = 0V, T<sub>a</sub> = 0°C to +70°C)

Parameter	Symbol	-13	-15	-17	Unit	Notes			
		Min	Max	Min					
Cycle Time	t <sub>CYC</sub>	13	-	15	-	17	-	ns	
Clock Access Time	t <sub>CD</sub>	-	6	-	7	-	8	ns	
Output Enable to Data Valid	t <sub>OE</sub>	-	5	-	6	-	7	ns	3
Clock HIGH to Output LOW-Z	t <sub>LZC</sub>	2	-	2	-	2	-	ns	1, 4
Output Hold from Clock HIGH	t <sub>OH</sub>	2	-	2	-	2	-	ns	1, 4
Output Enable LOW to Output LOW-Z	t <sub>LZOE</sub>	2	-	2	-	2	-	ns	1, 4
Output Enable HIGH to Output HIGH-Z	t <sub>HZOE</sub>	2	5	2	6	2	6	ns	1, 4
Clock HIGH to Output HIGH-Z	t <sub>HZC</sub>	-	5	-	6	-	6	ns	1, 4
Clock HIGH Pulse Width	t <sub>CH</sub>	4.5	-	5.5	-	6	-	ns	
Clock LOW Pulse Width	t <sub>CL</sub>	4.5	-	5.5	-	6	-	ns	
Address Setup to Clock HIGH	t <sub>AS</sub>	2.5	-	2.5	-	2.5	-	ns	5, 6
Address Status Setup to Clock HIGH	t <sub>SS</sub>	2.5	-	2.5	-	2.5	-	ns	5, 6
Data Setup to Clock HIGH	t <sub>DS</sub>	2.5	-	2.5	-	2.5	-	ns	5, 6
Write Setup to Clock HIGH	t <sub>WS</sub>	2.5	-	2.5	-	2.5	-	ns	5, 6
Address Advance Setup to Clock HIGH	t <sub>ADVS</sub>	2.5	-	2.5	-	2.5	-	ns	5, 6
Chip Select Setup to Clock HIGH	t <sub>CSS</sub>	2.5	-	2.5	-	2.5	-	ns	5, 6
Address Hold from Clock HIGH	t <sub>AH</sub>	0.5	-	0.5	-	0.5	-	ns	5, 6
Address Status Hold from Clock HIGH	t <sub>SH</sub>	0.5	-	0.5	-	0.5	-	ns	5, 6
Data Hold from Clock HIGH	t <sub>DH</sub>	0.5	-	0.5	-	0.5	-	ns	5, 6
Write Hold from Clock HIGH	t <sub>WH</sub>	0.5	-	0.5	-	0.5	-	ns	5, 6
Address Advance Hold from Clock HIGH	t <sub>ADVH</sub>	0.5	-	0.5	-	0.5	-	ns	5, 6
Chip Select Hold from Clock HIGH	t <sub>CSH</sub>	0.5	-	0.5	-	0.5	-	ns	5, 6

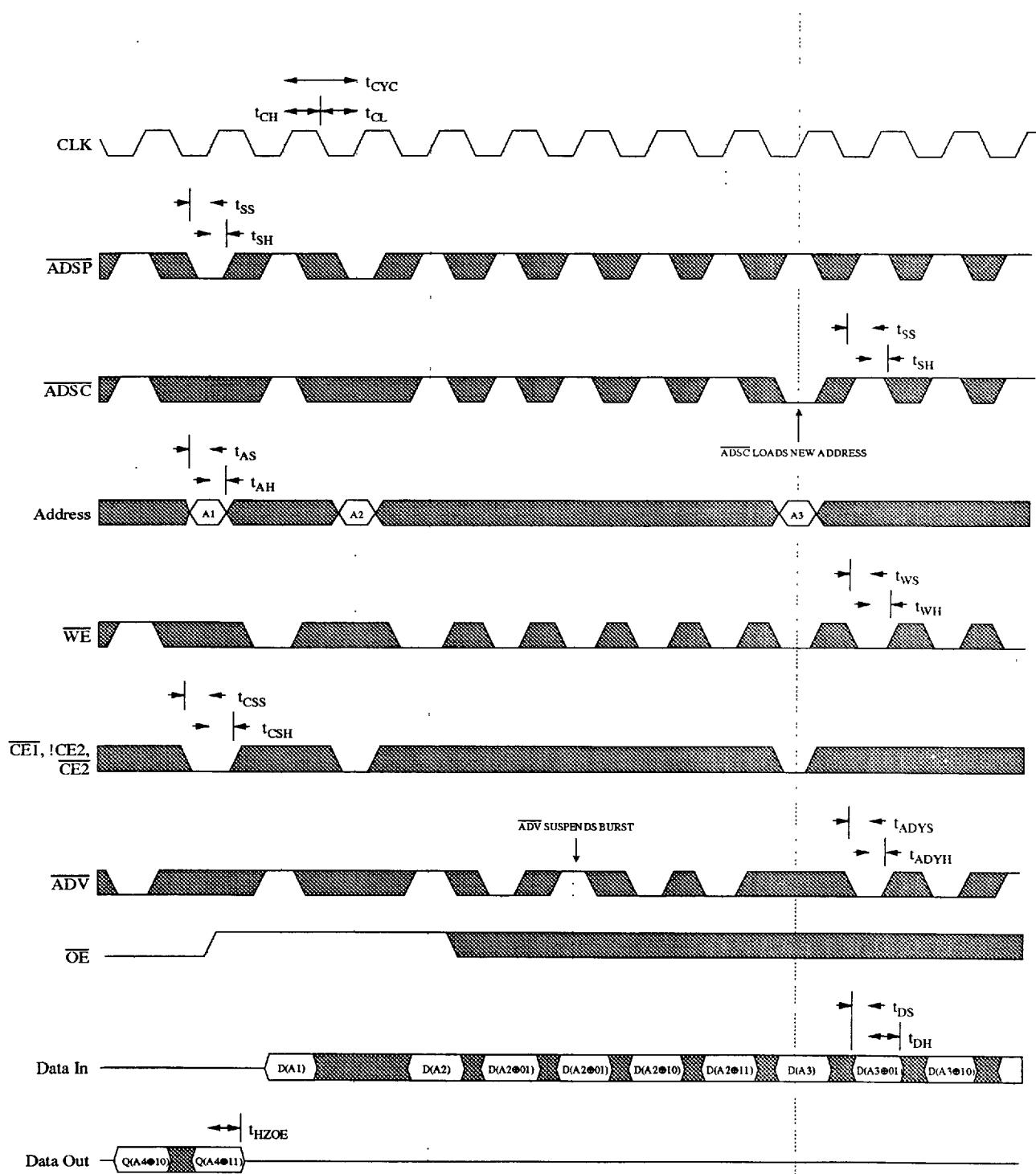


**TIMING WAVEFORM OF READ CYCLE**



Note:  $\oplus$  = XOR when MODE = HIGH/No Connect;  $\oplus$  = ADD when MODE = LOW. Refer to Burst Sequence Table, pg.3.

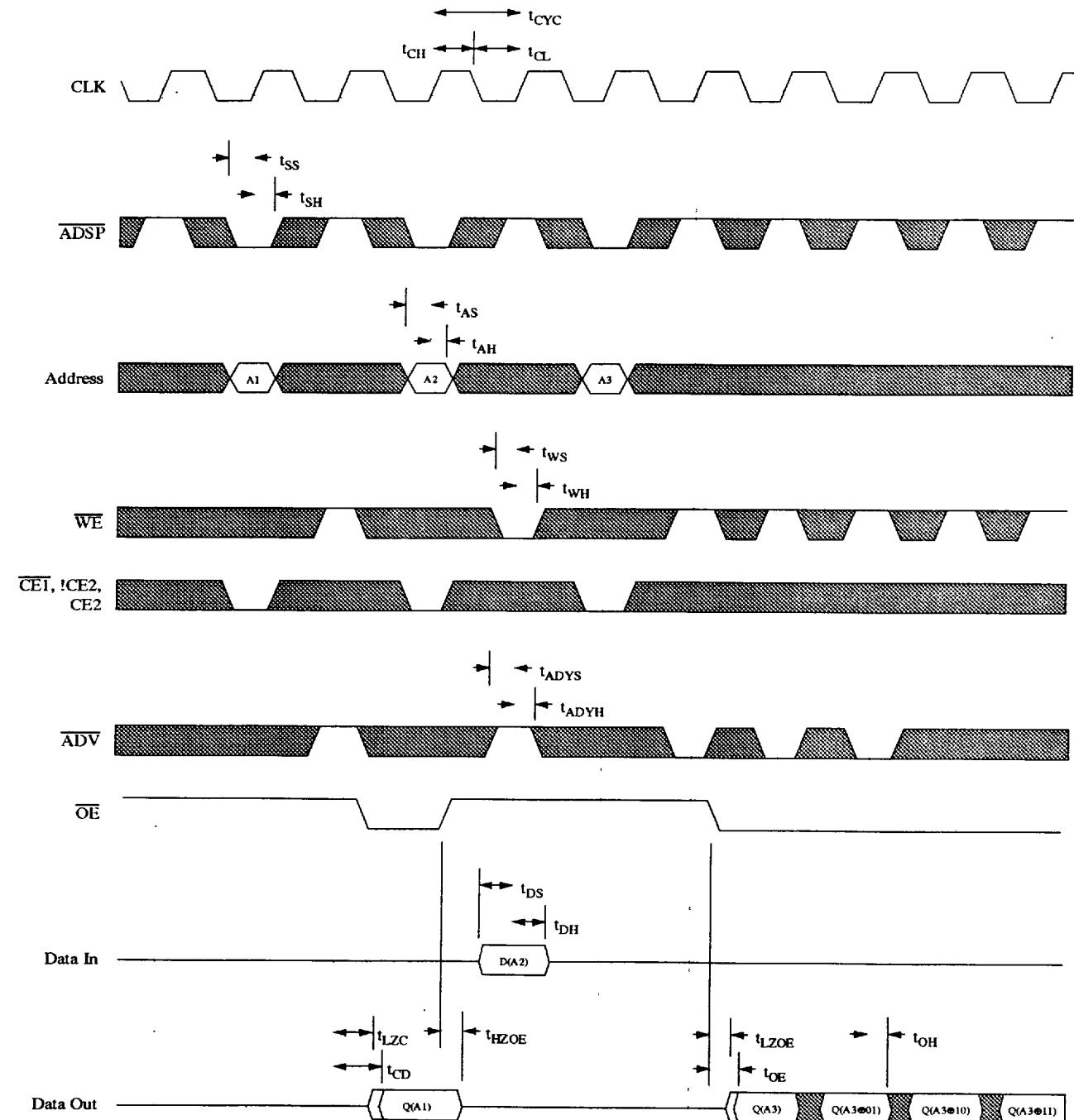
**TIMING WAVEFORM OF WRITE CYCLE**



Note:  $\oplus$  = XOR when MODE = HIGH/No Connect;  $\oplus$  = ADD when MODE = LOW. Refer to Burst Sequence Table, pg.3.



**TIMING WAVEFORM OF READ/WRITE CYCLE**



Note:  $\oplus$  = XOR when MODE = HIGH/No Connect;  $\oplus$  = ADD when MODE = LOW. Refer to Burst Sequence Table, pg.3.

**AC TEST CONDITIONS**

- Output Load: see Figure B,  
except for  $t_{LZC}$ ,  $t_{LZOE}$ ,  $t_{HZOE}$ ,  $t_{HZC}$  see Figure C.
- Input Pulse Level: GND to 3V. See Figure A.
- Input Rise and Fall Time (Measured at 0.3V and 2.7V): 2 ns. See figure A.
- Input and Output Timing Reference Levels: 1.5V.

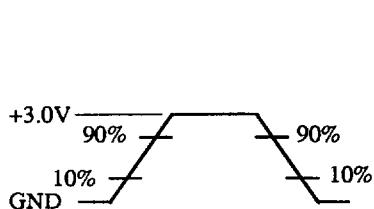


Figure A: Input Waveform

AS7C33232-06

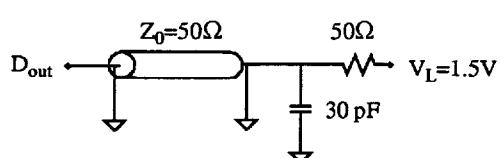
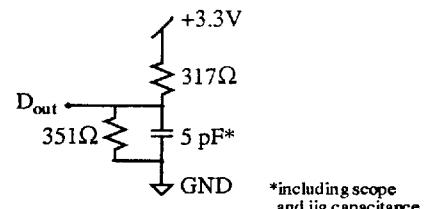


Figure B: Output Load (A)

AS7C33232-07

Figure C: Output Load(B)  
for  $t_{LZC}$ ,  $t_{LZOE}$ ,  $t_{HZOF}$ ,  $t_{HZC}$ 

AS7C33232-08

**NOTES**

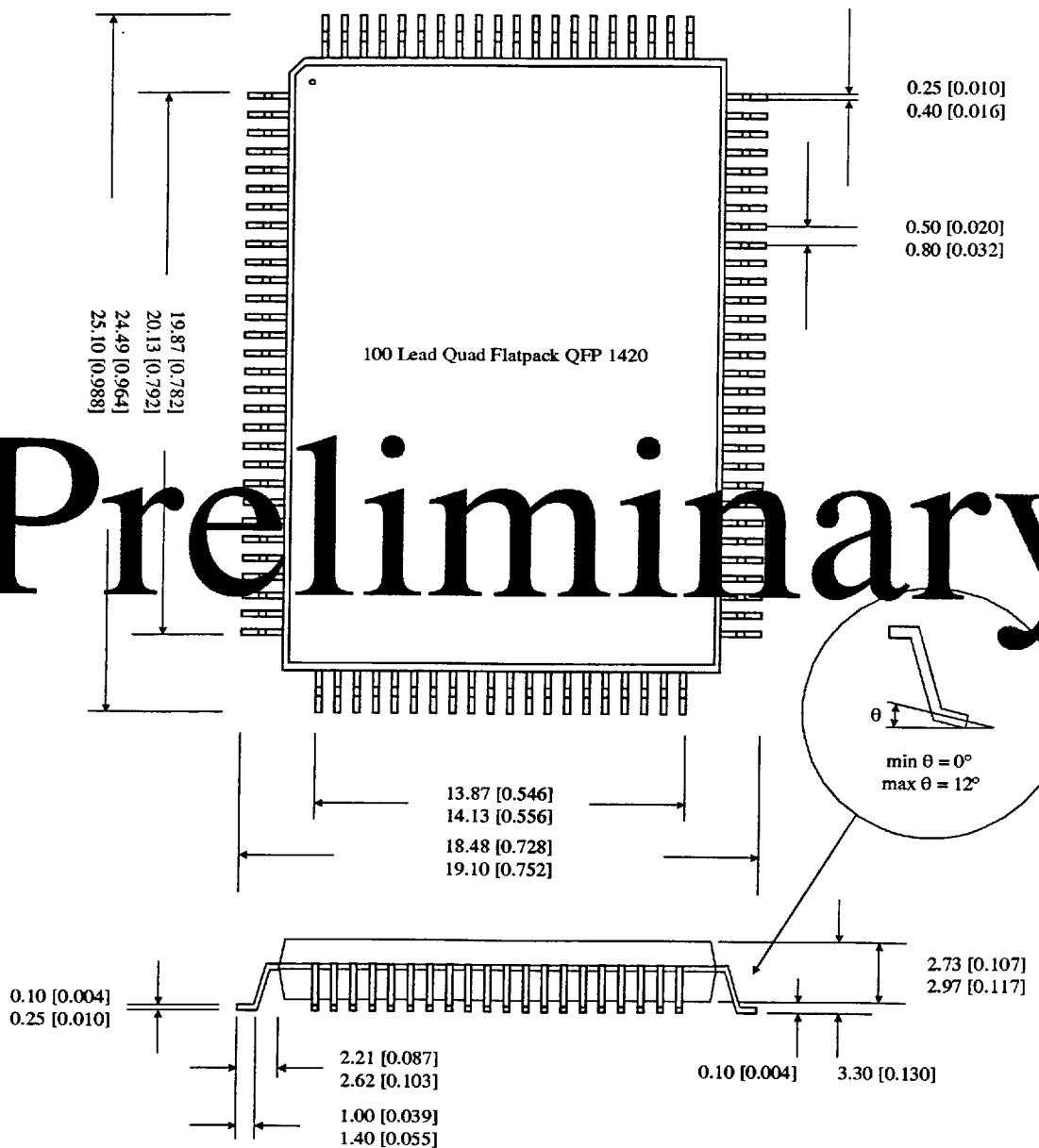
1. This parameter is guaranteed but not tested.
2. For test conditions, see *AC Test Conditions*, Figures A, B, C.
3.  $\overline{OE}$  state is ‘don’t care’ when a byte write enable is sampled LOW.
4. This parameter is sampled and not 100% tested.
5. A read cycle is defined as byte write enables all HIGH or  $\overline{ADSP}$  LOW for the required setup and hold times. A write cycle is defined as at least one byte write enable LOW and  $\overline{ADSP}$  HIGH for the required setup and hold times.
6. This is a synchronous device. All addresses must meet the specified setup and hold times for all rising edges of CLK when either ADSP or ADSC is LOW and chip enabled. All other synchronous inputs must meet the setup and hold times with stable logic levels for all rising edges of clock (CLK) when chip is enabled. Chip enable must be valid at each rising edge of CLK with either  $\overline{ADSP}$  or  $\overline{ADSC}$  LOW to remain enabled.



## PACKAGE DIMENSIONS

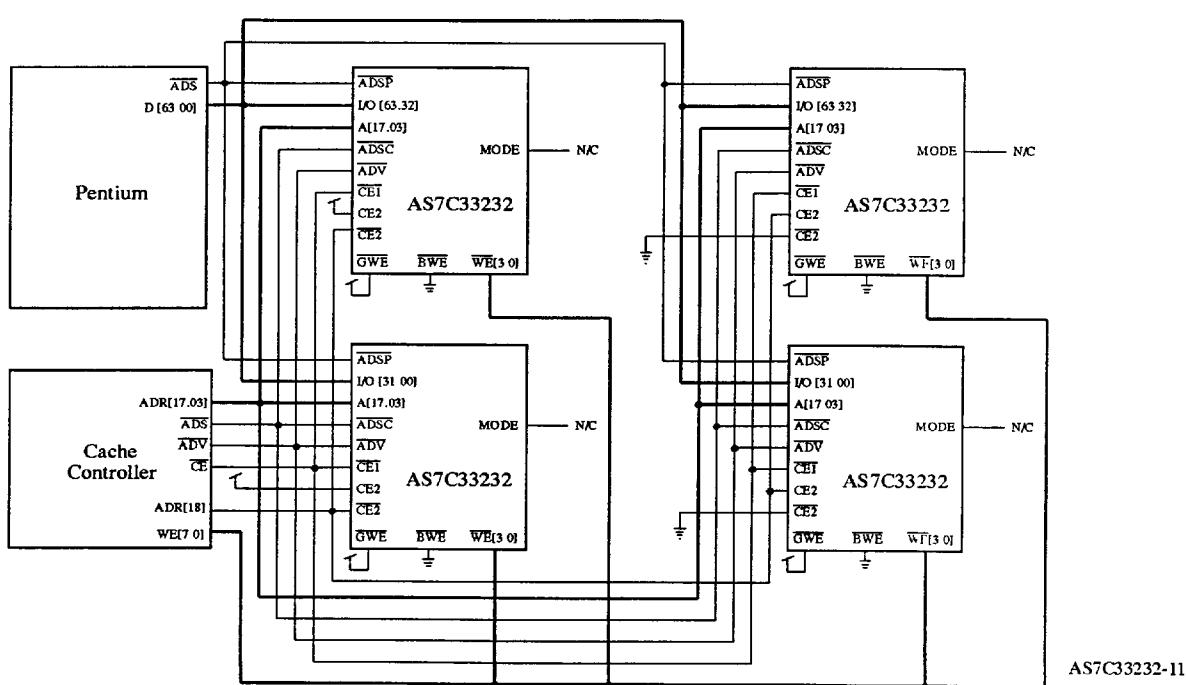
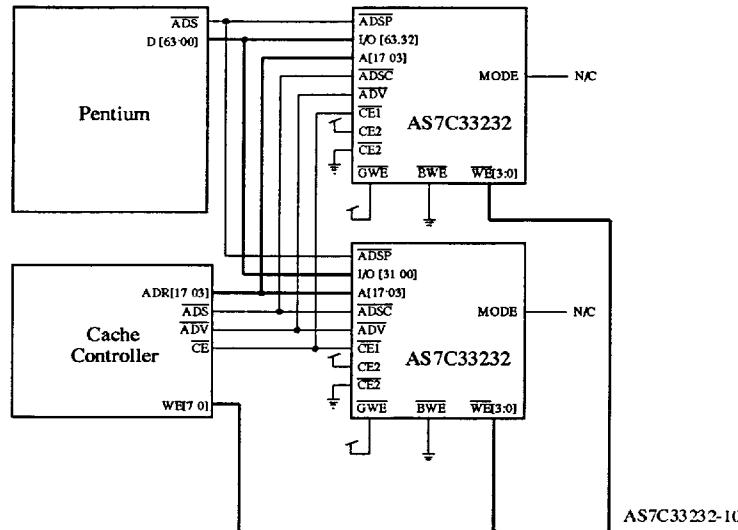
### Dimensions:

MIN mm. [MIN inches]  
MAX mm. [MAX inches]



AS7C33232-10

**APPLICATION CONNECTIVITY EXAMPLES**



**AS7C33232**  
**AS7C33232L**



### ORDERING INFORMATION

Package \ Min Cycle Time	13 ns	15 ns	17 ns
QFP 1420	AS7C33232-13QC AS7C33232L-13QC	AS7C33232-15QC AS7C33232L-15QC	AS7C33232-17QC AS7C33232L-17QC

### PART NUMBERING SYSTEM

AS7C	3	3232	X	-XX	Q	C	
SRAM Prefix	Blank 3	= 5V Supply = 3.3V Supply	Device Number	Blank L	= Std. Power = Low Power	Min Cycle Time Package: Q = QFP1420	Commercial Temperature Range, 0°C to 70°C

### REPRESENTATIVES, DISTRIBUTORS, AND SALES OFFICES

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<b>GEORGIA</b> Concord Component (404) 416-9597	MONTANA E <sup>2</sup> /Electronic Solutions (206) 637-0302	PENNSYLVANIA East: Vantage Sales (609) 424-6777 West: Midwest Marketing (216) 381-8575	INTERNATIONAL AUSTRALIA NJS Technology Pty Ltd. Mulgrave, Victoria +61-3-562-1244	KOREA Mirai Corporation Seoul, Korea +822-704-0300	<b>NORTHEAST AREA</b> Alliance Semiconductor Boston, MA (617) 239-8127
<b>HAWAII</b> Brooks Technical (415) 960-3880	NEVADA North: Brooks Technical (916) 965-3255	RHODE ISLAND Kitchen & Kutchin Inc. (617) 229-2660	BENELUX Britcomp Sales Oosterhout, Netherlands +31-1620-29851	TDI San Jose, CA USA +1-408-428-9177	
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### ALLIANCE SEMICONDUCTOR

3099 North First Street San Jose, CA 95134

(408) 383-4900 Fax (408) 383-4999

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June 1994

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